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PTO/SB/08A (04-03)

Approved for use 04-30-2003. OMB 0651-0031

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Sheet 1 Of 8

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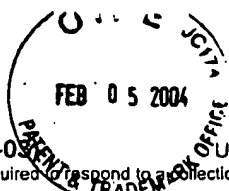
Application Number 10/078,473
Filing Date 2-21-02
First Named Inventor Ho Ki Kwon
Art Unit 2828
Examiner Name Dung T. Nguyen
Attorney Docket Number H0002992

U.S. PATENT DOCUMENTS

Table with 6 columns: Examiner Initials, Cite No, Document Number (Number, Kind Code), Publication Date, Name of Patentee or Applicant of Cited Document, Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear. Rows include US 4445218, US 4608697, US 4622672, US 4829347, US 4873696, US 4896325, US 5045499, US 5082799, US 5245622, US 5251225, US 5293392, US 5343487, US 5358880, US 5365540, US 5392307, US 5416044, US 5422901, US 5468343, US 5491710, US 5513204, US 5568504, US 5588995, US 5631472, US 5693180, US 5719891, US 5719894.

Examiner Signature [Signature] Date Considered 06/07/04

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Sheet	2	Of	8
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COMPLETE IF KNOWN

Application Number	10/078,473
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First Named Inventor	Ho Ki Kwon
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Examiner Name	Dung T. Nguyen
Attorney Docket Number	H0002992

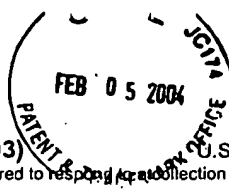
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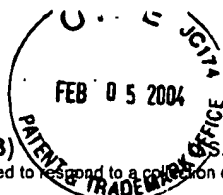
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Examiner Signature		Date Considered	06/07/04
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Sheet 4 Of 8

COMPLETE IF KNOWN

Application Number	10/078,473
Filing Date	2-21-02
First Named Inventor	Ho Ki Kwon
Group Art Unit	2828
Examiner Name	Dung T. Nguyen
Attorney Docket Number	H0002992

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No ¹	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear	T ⁶
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dw		EP	0 740 377	A1	10-30-1996	Hewlett-Packard Company		
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		WO	00/052789	A2	02-29-2000	The Regents of the University of California		
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		WO	01/017076	A2	03-08-2001	The Regents of the University of California		

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Application Number	10/078,473
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First Named Inventor	Ho Ki Kwon
Group Art Unit	2828
Examiner Name	Dung T. Nguyen
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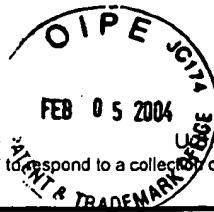
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First Named Inventor	Ho Ki Kwon
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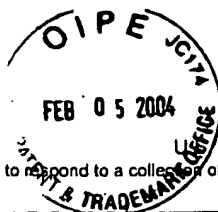
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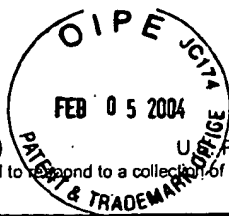
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Sheet 8 Of 8

COMPLETE IF KNOWN

Application Number	10/078,473
Filing Date	2-21-02
First Named Inventor	Ho Ki Kwon
Group Art Unit	2828
Examiner Name	Dung T. Nguyen
Attorney Docket Number	H0002992

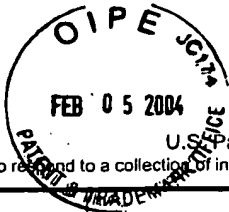
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COMPLETE IF KNOWN

Application Number	10/078,473
Filing Date	2/21/2002
First Named Inventor	Ho Ki Kwon
Art Unit	2828
Examiner Name	Dung T. Nguyen.
Attorney Docket Number	H0002992

U.S. PATENT DOCUMENTS

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		Number	Kind Code ² (if known)			
M ↓ ✓		US 5,659,180	A	08-19-1997	Shen et al.	
		US 5,679,963		10-21-1997	Klem et al.	
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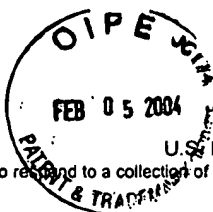
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M		WO	01/63708	A2	8-30-2001	Boucart et al.		X
		EP	0 715 357	A1	6-5-1996	McDermott		X
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<i>W</i>		B.T. McDermott et al., Appl. Phys. Lett. 68,1386 (1996), "Growth and doping of GaAsSb via MOCVD for InP HBTs"	
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